



ULC0544P10

Description

The ULC0544P10 is ultra low capacitance TVS arrays designed to protect high speed data interfaces. This series has been specifically designed to protect sensitive components which are connected to high-speed data and transmission lines from over-voltage caused by ESD (electrostatic discharge), CDE (Cable Discharge Events), and EFT (electrical fast transients).



Feature

- ♦ 50 Watts Peak Pulse Power per Line (tp=8/20µs)
- Protects Four High Speed Lines
- Low Clamping Voltage
- RoHS Compliant
- ♦ IEC61000-4-2(ESD):±15kV (air discharge) ±10kV (contact discharge);
- IEC61000-4-4 (EFT) 40A (5/50 η s)
- IEC61000-4-5 (LIGHTING) 2A (8/20 μ s)



Applications

- USB 3.0 / USB 3.1 Interfaces
- HDMI 1.4 / HDMI 2.0 Interfaces
- Video Graphics Cards
- Notebooks, Desktops, and Servers
- Portable Instrumentation
- Industrial Controls
- Peripherals

Mechanical Data

Functional Diagram

- DFN2510P10 (2.5x1.0mm) Package
- Molding Compound Flammability Rating : UL 94V-O
- Weight 5.0 Millgrams (Approximate)
- Quantity Per Reel : 3,000pcs
- Reel Size : 7 inch
- Lead Finish : Lead Free
- Device Marking: UL4L

Mechanical Characteristics

Symbol	Parameter	Value	Units
Ррр	Peak Pulse Power (tp=8/20µs waveform)	50	Watts
TJ	Operating Junction Temperature Range	-55 to +150	°C
Тѕтс	Storage Temperature Range	-55 to +150	°C
Τι	Soldering Temperature, T max = 10s	260	°C

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Electrical Characteristics (@ 25°C Unless Otherwise Specified)							
Characteristics	Symbol	Test Conditions		Тур.	Max.	Unit	
Reverse Working Voltage	V _{RWM}				5	V	
Reverse Breakdown Voltage	V _{BR}	I⊤=1mA	6			V	
Reverse Leakage Current	IR	V _{RWM} =5V ; T=25°C			1	μA	
Junction capacitance	CJ	I/O To GND; $V_R = 0V$, f=1MHz ;		0.35		pF	
Positive Clamping		I_{PP} =1A , T_{P} =8/20 μS ;			14		
Voltage	Vc	I _{PP} =2A,T _P =8/20μS;			25	V	

Characteristic Curves



Fig3. ESD Clamping Volatge & Peak Pulse Curerent



Fig2. ESD Pulse Waveform (according to IEC 61000-4-2)



Fig4. Pulse Waveform



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Transmission Line Pulse (TLP)

Transmission Line Pulse (TLP) is a measurement technique used in the Electrostatic Discharge (ESD) arena to characterize performance attributes of devices under ESD stresses. TLP is able to obtain current versus voltage (I–V) curves in which each data point is obtained with a 100 ns long pulse, with currents up to 40 A. TLP was first used in the ESD field to study human body model (HBM) in integrated circuits, but it is an equally valid tool in the field of system level ESD. The applicability of TLP to system level ESD is illustrated in Figure 1, which compares an 8 kV IEC 61000–4–2 current waveform with TLP current pulses of 8 and 16 A. The current levels and time duration for the pulses are similar and the initial rise time for the TLP pulse is comparable to the rise time of the IEC 61000–4–2's initial current spike. This application note will give a basic introduction to TLP measurements and explain the datasheet parameters extracted from TLP for Yeashin Technology's protection products.



Comparison of a Current Waveform of IEC 61000-4-2 with TLP Pulses at 8 and 16 A.

The IEC 61000-4-2 ESD waveforms is true to the Standard and is shown here as captured on an oscilloscope. The points A, B, and C show the points on the waveforms specified in IEC 61000-4-2.

TLP Characteristic



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Eye Diagram

1	Zero Level : measure of the mean value of the logical O.				
2	One Level : measure of the mean value of the logical 1.				
3	Rise Time : measure of the transition time of the				
	data from the 10% level to the 90% level on the				
	upward slope.				
4	Fall Time ; measure of the transition time of the				
	data from the 90% level to the 10% level on the				
	downward slope				
5	Eve Height : measure of the vertical opening				
0	Eye Height : measure of the vertical opening.				
6	Eve Width : measure of the horizontal opening				
0	Determine influence of iitter on the eve opening.				
7	Deterministic Titter: deviation of a transition				
/	from its ideal time caused by reflections relative				
	to other transitions				
8	Eve Amplitude : difference between the logic O				
0	level and the logic 1 level histogram mean value				
٩	Rit Date : inverse of the bit period				
,	Bit Rule : inverse of the bit period.				
	(7)				
-	<u>↓</u>				
\bigcirc					
(8)					
\sim					
	<u>↓</u>				

2

1

9

4





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Eye Diagram at 5Gbps and 10Gbps



High Speed Test : 10Gbps



Without Component



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DFN2510P10 Package Outline & Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	0.500	0.600	0.020	0.024	
A1	0.000	0.050	0.000	0.002	
A3	0.110REF.		0.004REF.		
D	2.450	2.550	0.096	0.100	
E	0.950	1.050	0.037	0.041	
D1	0.350	0.450	0.014	0.018	
E1	0.350	0.450	0.014	0.018	
k	0.150MIN.		0.006MIN.		
b	0.150	0.250	0.006	0.010	
е	0.500TYP.		0.020TYP.		
L	0.350	0.450	0.014	0.018	

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LAYOUT DIAGRAM INFORMATION



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